查询2SA1061供应商

Silicon Epitaxal Base Mesa Transistor

T-33-13
T-33-21

2SA1061 (PNP)
2SC2485 (NPN)

TOP-3 Package (See Page 36 For Dimensions)

2SA1061 (PNP)

Absolute Maximum Ratings (Ta=25°C)

Item	Symbol	Rating	Unit
Collector-Base Voltage	$-V_{CBO}$	100	V
Collector-Emitter Voltage	$-V_{CEO}$	100	V
Emitter-Base Voltage	$-V_{EBO}$	5	V
Collector Current	$-I_C$	6	A
Peak Collector Current	$-I_{CM}$	10	A
Collector Power Dissipation	P_C*	70	W
Junction Temperature	Tj	150	°C
Storage Temperature	Tstg	−55~+150	°C

*Tc=25°C

High Power Audio Frequency Amplifier Complementary Pair with 2SC2485

Feature:
• High collector power dissipation: 70W(Tc=25°C)

****h_{FE} Classification**

h_{FE}	100~200	60~120	40~80
Class	P	Q	R

Electrical Characteristics (Ta=25°C)

Item	Symbol	Condition	min.	typ.	max.	Unit
Collector Cutoff Current	$-I_{CBO}$	$-V_{CB}$=100V, I_E=0			50	μA
Emitter Cutoff Current	$-I_{EBO}$	$-V_{EB}$=3V, I_C=0			50	μA
DC Current Gain	h_{FE1}	$-V_{CE}$=5V, $-I_C$=0.2A	20			
	h_{FE2}**	$-V_{CE}$=5V, $-I_C$=1.0A	40		220	V
	h_{FE3}	$-V_{CE}$=5V, $-I_C$=4A	20			
Base Emitter Voltage	$-V_{BE}$	$-V_{CE}$=5V, $-I_C$=4A			1.8	V
Collector-Emitter Saturation Voltage	$-V_{CE(sat)}$	$-I_C$=4A, $-I_B$=0.4A			2.0	V
Gain Bandwidth Product	f_T	$-V_{CE}$=5V, $-I_C$=0.5A		20		MHz

2SC2485 (NPN)

Absolute Maximum Ratings (Ta=25°C)

Item	Symbol	Rating	Unit
Collector-Base Voltage	V_{CBO}	100	V
Collector-Emitter Voltage	V_{CEO}	100	V
Emitter-Base Voltage	V_{EBO}	5	V
Collector Current	I_C	6	A
Peak Collector Current	I_{CM}	10	A
Collector Power Dissipation	P_C*	70	W
Junction Temperature	Tj	150	°C
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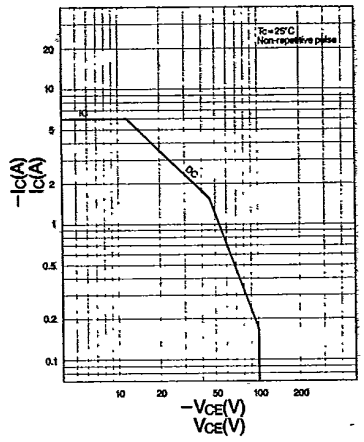
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	I_C=4A, I_B=0.4A			2.0	V
Gain Bandwidth Product	f_T	V_{CE}=5V, I_C=0.5A		20		MHz

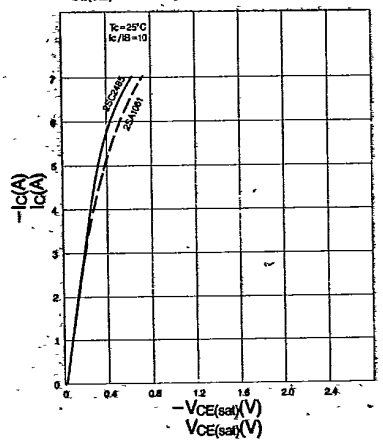
2SA1061 (PNP)
2SC2485 (NPN)

Typical Characteristics

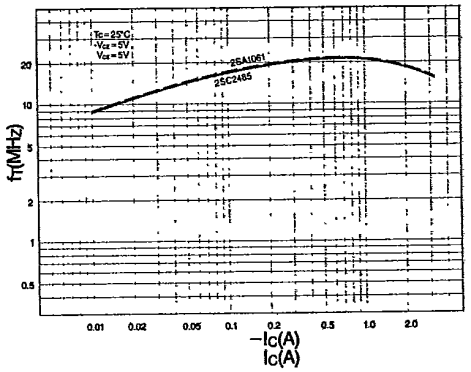
Area of Safe Operation (ASO) (Tc=25°C)



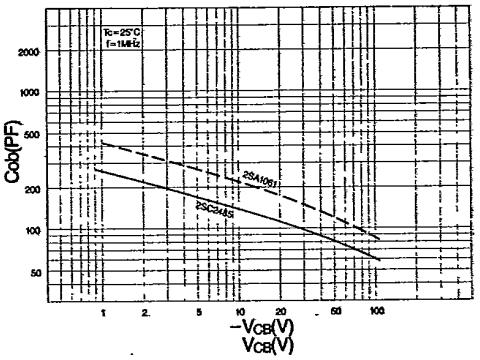
$V_{CE(sat)}$ vs. Ic characteristics



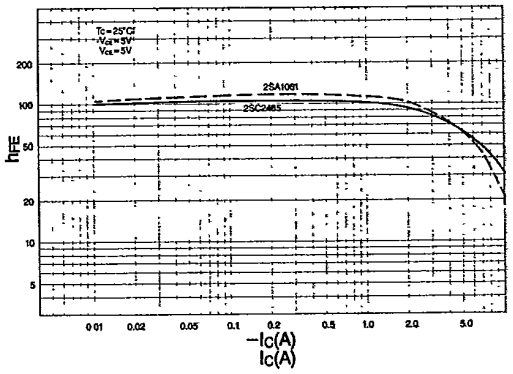
f_T vs. Ic characteristics



Cob vs. V_{CB} characteristics



h_{FE} vs Ic characteristics



V_{BE} vs. Ic characteristics